

Excellent Integrated System Limited

Stocking Distributor

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ON Semiconductor 80SQ045NRL

For any questions, you can email us directly: sales@integrated-circuit.com



80SQ045N

Preferred Device

Axial Lead Rectifier

These devices employ the Schottky Barrier principle in a large area metal-to-silicon power diode. State-of-the-art geometry features epitaxial construction with oxide passivation and metal overlap contact. Ideally suited for use as rectifiers in low-voltage, high-frequency inverters, free wheeling diodes, and polarity protection diodes.

Features

- High Current Capability
- Low Stored Charge, Majority Carrier Conduction
- Low Power Loss/High Efficiency
- Highly Stable Oxide Passivated Junction
- Guard-Ring for Stress Protection
- Low Forward Voltage
- High Surge Capacity
- These are Pb-Free Devices*

Mechanical Characteristics:

- Case: Epoxy, Molded
- Weight: 1.1 Gram (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 220°C Max. for 10 Seconds, 1/16" from Case
- Polarity: Cathode indicated by Polarity Band
- ESD Protection: Human Body Model > 4000 V (Class 3) Machine Model > 400 V (Class C)

MAXIMUM RATINGS

Rating	Symbol	Max	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	45	V
Average Rectified Forward Current T _L = 75°C (Psi _{JL} = 12°C/W, P.C. Board Mounting, Note 2)	I _O	8.0	A
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I _{FSM}	140	Α
Operating and Storage Junction Temperature Range (Reverse Voltage Applied)	T _J , T _{stg}	-65 to +125	°C
Voltage Rate of Change (Rated V _R)	dv/dt	10	V/ns

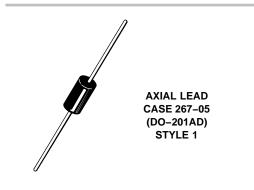
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



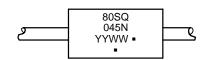
ON Semiconductor®

http://onsemi.com

SCHOTTKY BARRIER RECTIFIER 8.0 AMPERES



MARKING DIAGRAM



= Year

= Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]	
80SQ045N	Axial Lead*	500 Units/Box	
80SQ045NG	Axial Lead*	500 Units/Box	
80SQ045NRL	Axial Lead*	1500/Tape & Reel	
80SQ045NRLG	Axial Lead*	1500/Tape & Reel	

- †For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
- *This package is inherently Pb–Free.

Preferred devices are recommended choices for future use and best overall value.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

80SQ045N

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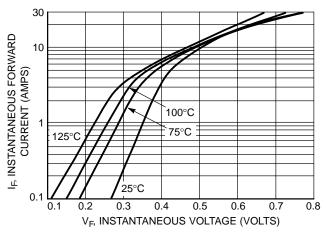
THERMAL CHARACTERISTICS

Characteristic		0.9 in x 0.9 in Copper Pad Size	6.75 in x 6.75 in Copper Pad Size	Unit
Thermal Resistance, Junction–to–Lead (See Note 2 – Mounting Data)	$R_{\theta JL}$	13	12	°C/W
Thermal Resistance, Junction-to-Ambient (See Note 2 - Mounting Data)	$R_{\theta JA}$	50	40	

ELECTRICAL CHARACTERISTICS (T_L = 25°C unless otherwise noted)

Characteristic	Symbol	Max	Unit
Maximum Instantaneous Forward Voltage (Note 1) $(i_F = 8.0 \text{ A}, T_L = 25^{\circ}\text{C})$	V _F	0.55	V
Maximum Instantaneous Reverse Current @ Rated dc Voltage (Note 1) $T_L = 25^{\circ}C$ $T_L = 100^{\circ}C$	i _R	1.0 50	mA

^{1.} Pulse Test: Pulse Width = 300 μ s, Duty Cycle = 2.0%.



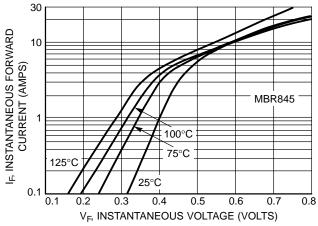
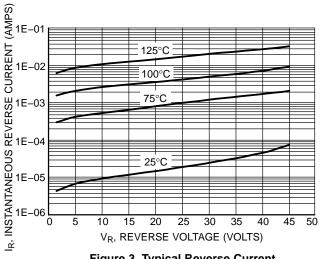


Figure 1. Typical Forward Voltage

Figure 2. Maximum Forward Voltage



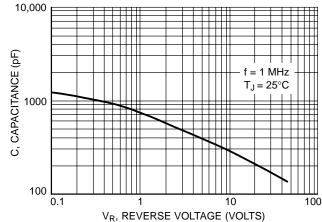


Figure 3. Typical Reverse Current

Figure 4. Typical Capacitance

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Datasheet of 80SQ045NRL - DIODE SCHOTTKY 45V 8A DO201AA

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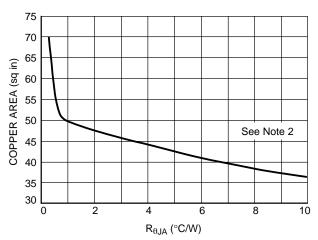


Figure 5. $R_{\theta JA}$ versus Copper Area

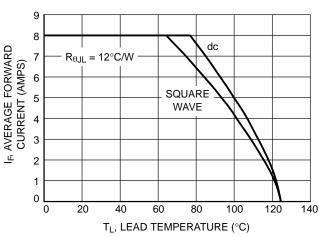


Figure 6. Current Derating - Lead

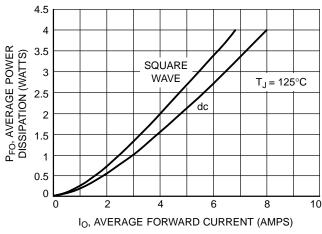
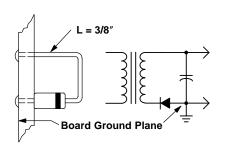


Figure 7. Forward Power Dissipation

NOTE 2 — MOUNTING DATA

Mounting Method

P.C. Board with 6.75 sq. in. copper surface.



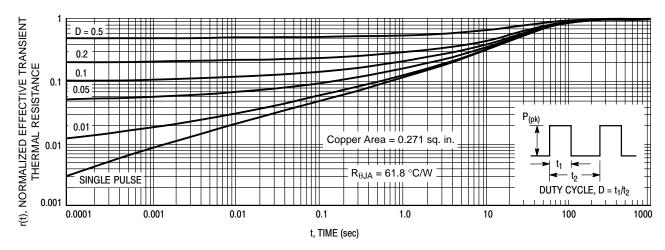


Figure 8. Thermal Response, Junction-to-Ambient



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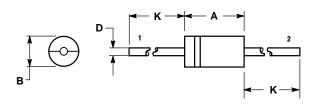
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PACKAGE DIMENSIONS

AXIAL LEAD CASE 267-05 **ISSUE G**



- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.287	0.374	7.30	9.50
В	0.189	0.209	4.80	5.30
D	0.047	0.051	1.20	1.30
K	1.000		25.40	

STYLE 1: PIN 1. CATHODE (POLARITY BAND) 2. ANODE

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